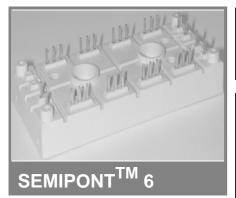
SKD 146/..-L75



3-Phase Bridge Rectifier + IGBT braking chopper

SKD 146/..-L75

Target Data

Features

- · Compact design
- · Two screws mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- High surge currents
- Up to 1600V reverse voltage
- UL recognized, file no. E 63 532

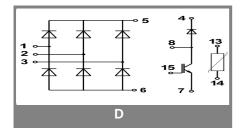
Typical Applications

- DC drives
- Controlled filed rectifiers for DC motors
- Controlled battery charger

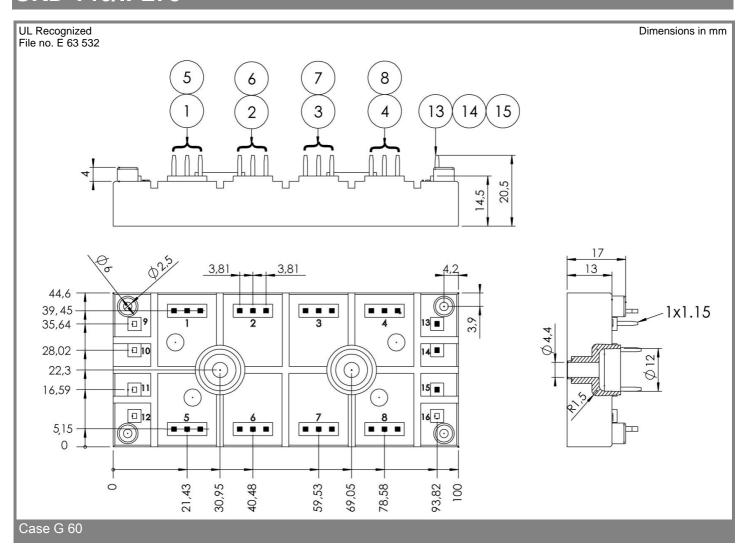
V_{RSM}	V_{RRM}, V_{DRM}	I _D = 140 A (maximum value for continuous operation)		
V	V	(T _s = 85 °C)		
1200	1300	SKD 146/12-L75		
1600	1700	SKD 146/16-L75		

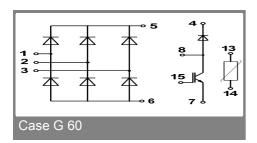
Absolute	Maximum Ratings	T_s = 25 °C, unless otherwise s	r _s = 25 °C, unless otherwise specified				
Symbol	Conditions	Values	Units				
Bridge - Rectifier							
I _D	T _s = 85 °C; inductive load	140	Α				
I_{FSM}/I_{TSM}	$t_p = 10 \text{ ms}; \sin 180^\circ; T_{jmax}$	1250	Α				
i²t	$t_p = 10 \text{ ms}; \sin 180^\circ; T_{jmax}$	7800	A²s				
IGBT - Chopper							
V_{CES}/V_{GES}		1200 / 20	V				
I _C	T _s = 25 (70) °C	100 (75)	Α				
I _{CM}	$t_p = 1 \text{ ms; } T_s = 25 (70) ^{\circ}\text{C}$	200 (150)	Α				
Freewheeling - CAL Diode							
V_{RRM}		1200	V				
I _F	T _s = 25 (70) °C	90 (70)	Α				
I _{FM}	$t_p = 1 \text{ ms; } T_s = 25 (70) ^{\circ}\text{C}$	180 (140)	Α				
T_{v_i}	Diode & IGBT (Thyristor)	- 40 + 150 (0 + 125)	°C				
T _{stg}		- 40 + 125	°C				
T _{solder}	terminals, 10 s	260	°C				
V _{isol}	a.c. (50) Hz, RMS 1 min. / 1 s	3000 / 3600	V				

Characteristics		$T_s = 25 ^{\circ}C$	T_s = 25 °C, unless otherwise specified					
Symbol	Conditions	min.	typ.	max.	Units			
Diode - Rectifier								
V_{TO} / r_{t}	T _j = 125 °C		0,8 / 4		V / $m\Omega$			
$R_{th(j-s)}$	per diode			0,8	K/W			
IGBT - CI	IGBT - Chopper							
V _{CE(sat)}	I _C = 75 A, T _j = 25 °C; V _{GE} = 15 V		2,35		V			
$R_{th(j-s)}$	per IGBT			0,4	K/W			
t _{d(on)} / t _r	valid for all values:		70 / 50		ns			
t _{d(off)} / t _f	V _{CC} = 600 V; V _{GE} = 15 V; I _C = 75 A; T _j = 125 °C;		450 / 45		ns			
$E_{on} + E_{off}$	$T_{j} = 125 ^{\circ}\text{C}; R_{G} = 12 \Omega;$		16		mJ			
	inductive load							
CAL - Did	ode - Freewheeling				•			
$V_{T(TO)} / r_t$	T _i = 125 °C		1 / 11	1,2 / 15	V / mΩ			
R _{th(j-s)}	per diode			0,8	K/W			
I _{RRM}	valid for all values:		75		Α			
Q _{rr}	$I_F = 75 \text{ A}; V_R =600 \text{ V};$ $dI_F/dt =800 \text{ A/}\mu\text{s}$		11		μC			
E _{off}	V _{GE} = 0 V; T _j = 125 °C				mJ			
Tempera	ture Sensor	•			•			
R _{TS}	T = 25 (100) °C;	1	000 (1670)		Ω			
Mechanical data								
M_S	mounting Torque	2,5		3,5	Nm			



SKD 146/..-L75





This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

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